

XPT IGBT

preliminary

$$V_{CES} = 1200V$$

$$I_{C25} = 9A$$

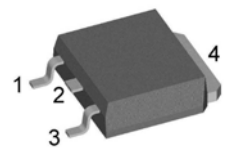
$$V_{CE(sat)} = 1.8V$$

Copack

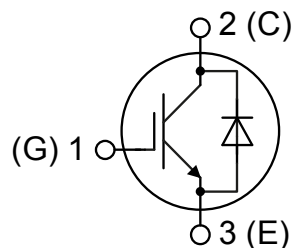
Part number

IXA4IF1200UC

Marking on Product: X4TAUF



Backside: collector



Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_C
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package: TO-252 (DPak)

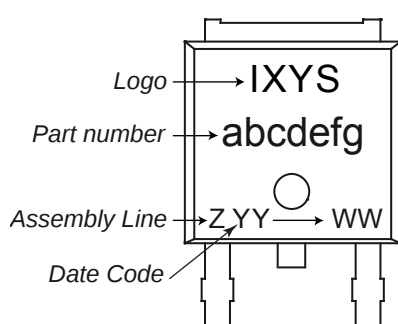
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IGBT				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{CES}	collector emitter voltage	T _{VJ} = 25°C				1200	V	
V _{GES}	max. DC gate voltage					±20	V	
V _{GEM}	max. transient gate emitter voltage					±30	V	
I _{C25}	collector current	T _C = 25°C				9	A	
I _{C100}		T _C = 100°C				5	A	
P _{tot}	total power dissipation	T _C = 25°C				45	W	
V _{CE(sat)}	collector emitter saturation voltage	I _C = 3A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C		1.8 2.1	2.1	V V	
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.1mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	5.4	5.9	6.5	V	
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C			0.1	mA mA	
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V				500	nA	
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 3 A			12		nC	
t _{d(on)}	turn-on delay time	inductive load T_{VJ} = 125°C V_{CE} = 600V; I_C = 3A V_{GE} = ±15 V; R_G=330 Ω			70		ns	
t _r	current rise time					40		ns
t _{d(off)}	turn-off delay time					250		ns
t _f	current fall time					100		ns
E _{on}	turn-on energy per pulse					0.4		mJ
E _{off}	turn-off energy per pulse					0.3		mJ
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G =330 Ω	T _{VJ} = 125°C					
I _{CM}		V _{CEmax} = 1200V				9	A	
SCSOA	short circuit safe operating area	V _{CEmax} = 900 V						
t _{sc}	short circuit duration	V _{CE} = 900 V; V _{GE} = ±15 V	T _{VJ} = 125°C			10	μs	
I _{sc}	short circuit current	R _G = 330 Ω; non-repetitive			12		A	
R _{thJC}	thermal resistance junction to case					2.7	K/W	
R _{thCH}	thermal resistance case to heatsink				0.50		K/W	
Diode								
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 25°C				1200	V	
I _{F25}	forward current	T _C = 25°C				10	A	
I _{F100}		T _C = 100°C				6	A	
V _F	forward voltage	I _F = 3A	T _{VJ} = 25°C T _{VJ} = 125°C			2.20	V V	
					1.90			
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C			*	mA mA	
	* not applicable, see Ices value above				*			
Q _{rr}	reverse recovery charge	V_R = 600 V -di_F/dt = -150 A/μs I_F = 3A; V_{GE} = 0 V	T _{VJ} = 125°C			0.5		μC
I _{RM}	max. reverse recovery current					5		A
t _{rr}	reverse recovery time					350		ns
E _{rec}	reverse recovery energy					0.1		mJ
R _{thJC}	thermal resistance junction to case					3	K/W	
R _{thCH}	thermal resistance case to heatsink				0.50		K/W	

preliminary

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			20	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				0.3		g
F_c	mounting force with clip		20		60	N

Product Marking



Part number

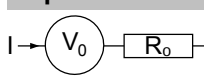
I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 4 = Current Rating [A]
 IF = Copack
 1200 = Reverse Voltage [V]
 UC = TO-252AA (DPak)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA4IF1200UC	X4TAUF	Tape & Reel	2500	510217

Similar Part	Package	Voltage class
IXA4IF1200TC	TO-268AA (D3Pak) (2)	1200

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150\text{ °C}$

 $V_{0\text{ max}}$ threshold voltage

 $R_{0\text{ max}}$ slope resistance *

IGBT

1.1

460

Diode

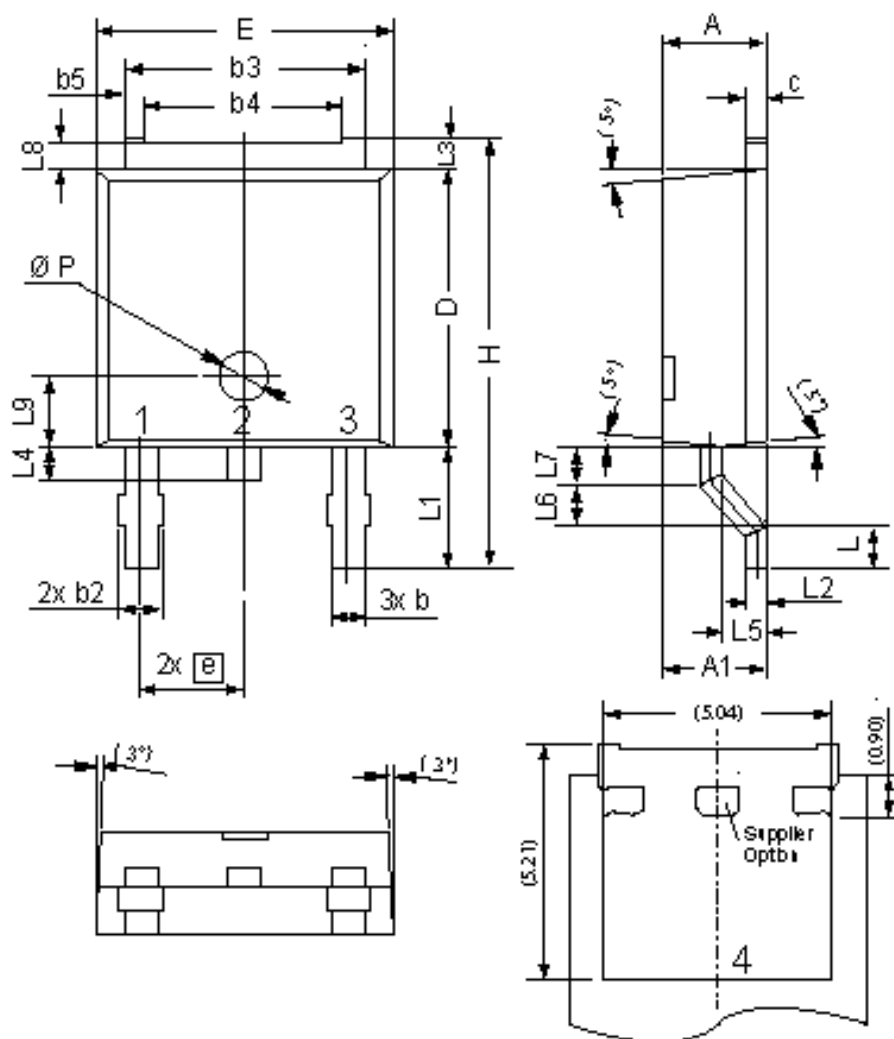
1.25

280

V

mΩ

Outlines TO-252 (DPak)



Dim	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34 BSC		0.171 BSC	
b5	0.50 BSC		0.020 BSC	
c	0.40	0.86	0.016	0.034
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	10.10	0.362	0.398
L	0.55	1.28	0.022	0.050
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50 BSC		0.059 BSC	
Ø P	1.00 BSC		0.039 BSC	

